## **SKKD 205F, SKND 205F**



SEMIPACK<sup>®</sup> 2

Fast Diode Modules

## SKKD 205F SKND 205F

Preliminary Data

## Features

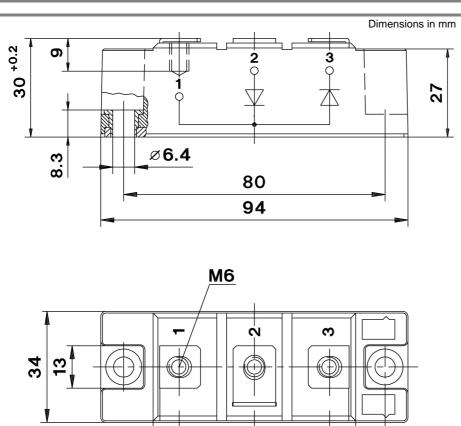
- Very soft recovery over the whole current range
- Very short recovery times
- Low switching losses
- Heat transfer through ceramic isolated metal baseplate
- Materials and distances according to UL

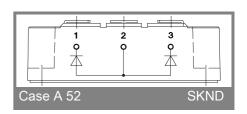
## **Typical Applications**

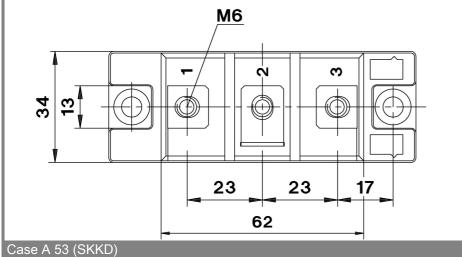
- Self-commutated inverters
- DC choppers
- AC motor speed control
- Inductive heating
- Uninterruptible power supplies
- Electronic welders
- General power switching applications

| V <sub>RSM</sub> | V <sub>RRM</sub> | I <sub>FRMS</sub> = 455 A (maximum value for continuous operation) |             |  |
|------------------|------------------|--|-------------|--|
| V                | V                | I <sub>FAV</sub> = 205 A (sin. 180; 50 Hz; T <sub>c</sub> = 87 °C) |             |  |
| 600              | 600              | SKKD 205F06  | SKND 205F06 |  |

| Symbol               | Conditions  | Values      | Units |
|----------------------|---|-------------|-------|
| I <sub>FAV</sub>     | sin. 180; T <sub>c</sub> = 87 °C                            | 205         | А     |
| I <sub>FSM</sub>     | T <sub>vi</sub> = 25 °C; 10 ms ms                           | 3500        | А     |
| _                    | T <sub>vi</sub> = 150 °C; 10 ms ms                          | 3000        | А     |
| i²t                  | T <sub>vj</sub> = 25 °C; 8,3 10 ms                          | 61250       | A²s   |
|                      | T <sub>vj</sub> = 150 °C; 8,3 10 ms                         | 45000       | A²s   |
| V <sub>F</sub>       | T <sub>vi</sub> = 25 °C; I <sub>F</sub> = 400 A             | max. 1,3    | V     |
| V <sub>(TO)</sub>    | T <sub>vj</sub> = 150 °C                                    | max. 0,9    | V     |
| r <sub>T</sub>       | $T_{vj} = 150 \ ^{\circ}C$                                  | max. 2      | mΩ    |
| I <sub>RD</sub>      | $T_{vj} = 25 \text{ °C}; V_{RD} = V_{RRM}$                  | max. 0,4    | mA    |
| I <sub>RD</sub>      | T <sub>vj</sub> = 150 °C; V <sub>RD</sub> =V <sub>RRM</sub> | max. 30     | mA    |
| Q <sub>rr</sub>      | T <sub>vi</sub> = 150 °C, I <sub>F</sub> = 300 A,           | 25          | μC    |
| I <sub>RM</sub>      | -di/dt = 800 A/µs, V <sub>R</sub> = 300 V                   | 120         | А     |
| t <sub>rr</sub>      |   | 130         | ns    |
| E <sub>rr</sub>      |   | -           | mJ    |
| R <sub>th(j-c)</sub> | per diode / per module                                      | 0,16 / 0,08 | K/W   |
| R <sub>th(c-s)</sub> | per diode / per module                                      | 0,1 / 0,05  | K/W   |
| T <sub>vj</sub>      |   | - 40 + 150  | °C    |
| T <sub>stg</sub>     |   | - 40 + 125  | °C    |
| V <sub>isol</sub>    | a.c. 50 Hz; r.m.s.; 1 s / 1 min.                            | 3600 / 3000 | ٧~    |
| M <sub>s</sub>       | to heatsink   | 5 ± 15 %    |       |
| Mt                   | for terminals   | 5 ± 15 %    |       |
| а                    |   | 5 * 9,81    | m/s²  |
| m                    | approx.   | 250         | g     |
| Case                 | SKND  | A 52        |       |
|                      | SKKD  | A 53        |       |
|                      |   |             |       |







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